

MMBD202CC

PRV : 80 Volts
Io : 100 mA

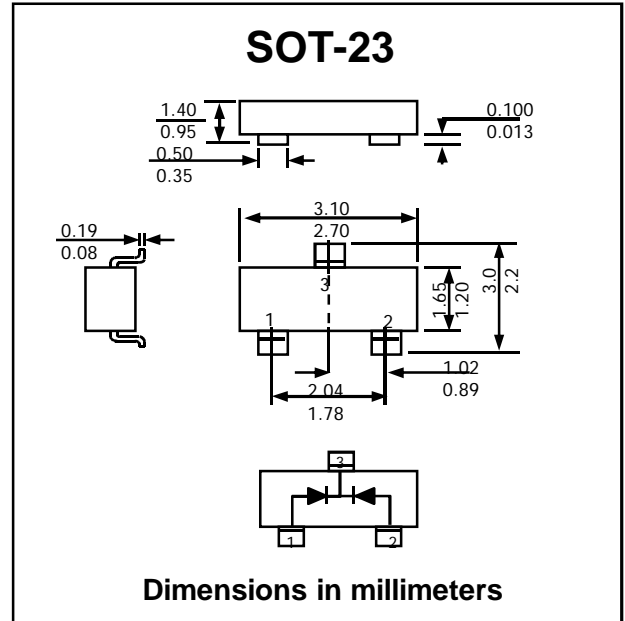
APPLICATION :

- * Silicon Epitaxial Planar Switching Diode
- * Ultra high speed switching

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : A4

SILICON EPITASIAL PLANAR SWITCHING DIODE



ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

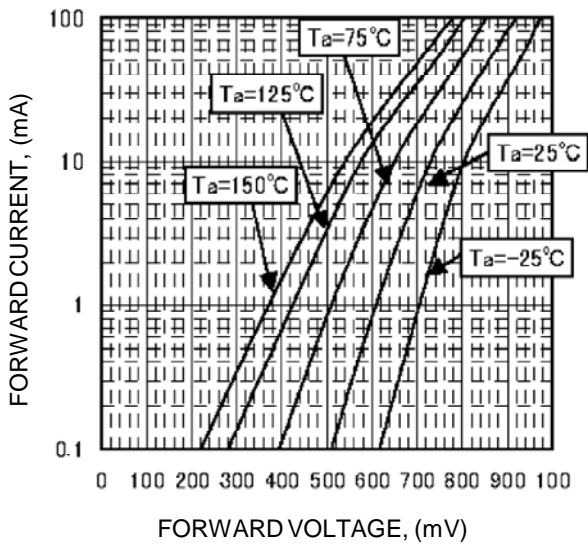
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V _{RM}	80	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non -Repetitive Peak Forward Surge Current (t = 1 μs)	I _{FSM}	4.0	A
Total Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tj = 25 °C)

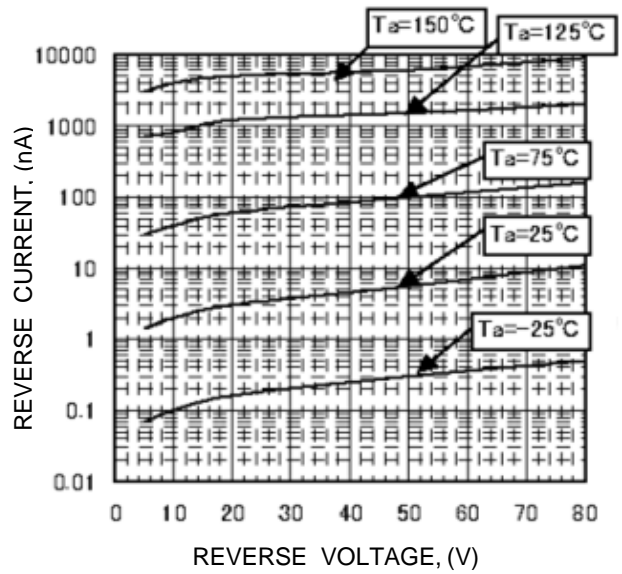
Parameter	Test Condition	Symbol	Min.	Max.	Unit
Forward Voltage	I _F = 100 mA	V _F	-	1.2	V
Reverse Current	V _R = 70 V	I _R	-	0.1	μA
Total Capacitance	V _R = 6 V, f = 1 MHz	C _T	-	3.5	pF
Reverse Recovery Time	I _F = 5 mA, V _R = 6 V R _L = 50 Ω	T _{rr}	-	4	ns

RATINGS AND CHARACTERISTIC CURVES (MMBD202CC)

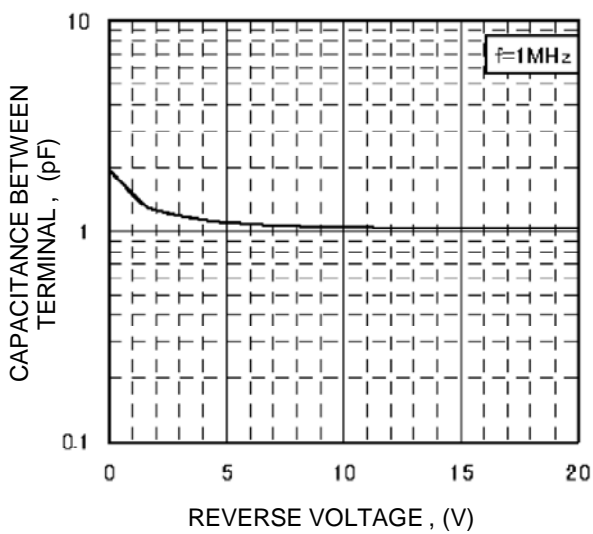
$V_F - I_F$ CHARACTERISTICS



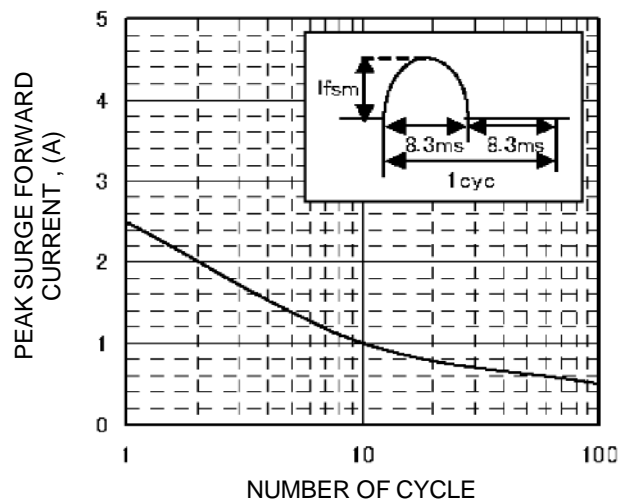
$V_R - I_R$ CHARACTERISTICS



V_R vs C_T CHARACTERISTICS

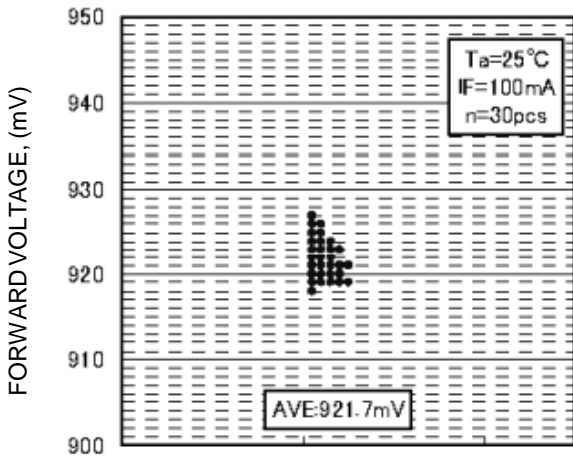


I_{FSM} - CYCLE CHARACTERISTICS

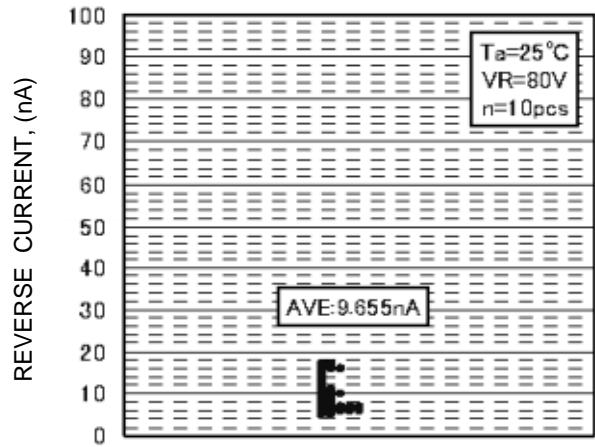




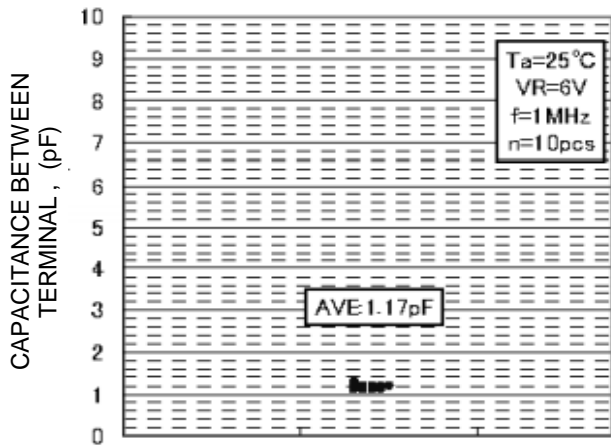
RATINGS AND CHARACTERISTIC CURVES (MMBD202CC)



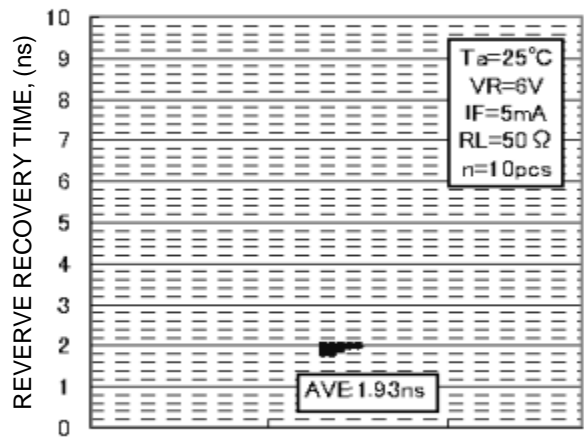
VF DISPERSION MAP



VF DISPERSION MAP



Ct DISPERSION MAP



trr DISPERSION MAP